

NCP3231B

Buck Converter - Synchronous, High Current

The NCP3231B is a high current, high efficiency, voltage-mode synchronous buck converter which operates from 4.5 V to 18 V input and generates output voltages down to 0.6 V at up to 25 A.

Features

- Wide Input Voltage Range from 4.5 V to 18 V
- 0.6 V Internal Reference Voltage
- 1 MHz Switching Frequency
- External Programmable Soft-start
- Lossless Low-side FET Current Sensing
- Output Over-voltage Protection and Under-voltage Protection
- System Over-temperature Protection using a Thermistor or Sensor
- Hiccup Mode Operation for All Faults
- Pre-bias Start-up
- Adjustable Output Voltage
- Power Good Output
- Internal Over-temperature Protection
- This is a Pb-Free Device*

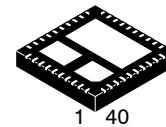
Typical Applications

- Cellular Base Stations
- ASIC, FPGA, DSP and CPU Core and I/O Supplies
- Telecom and Network Equipment
- Server and Storage System



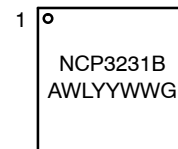
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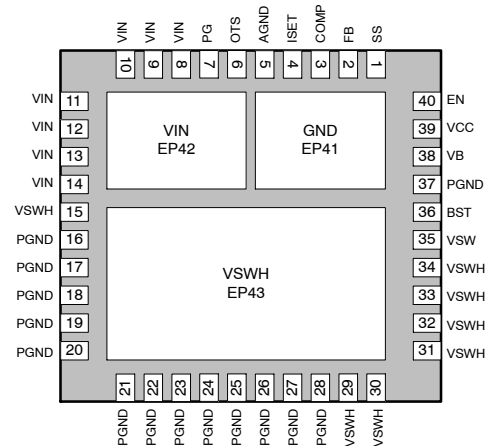
**QFN40 6x6, 0.5P
CASE 485CM**

MARKING DIAGRAM



NCP3231B = Specific Device Code
 A = Assembly Location
 WL = Wafer Lot
 YY = Year
 WW = Work Week
 G = Pb-Free Package

PIN CONNECTIONS



(TOP VIEW)

ORDERING INFORMATION

Device	Package	Shipping†
NCP3231BMNTXG	QFN40 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NCP3231B

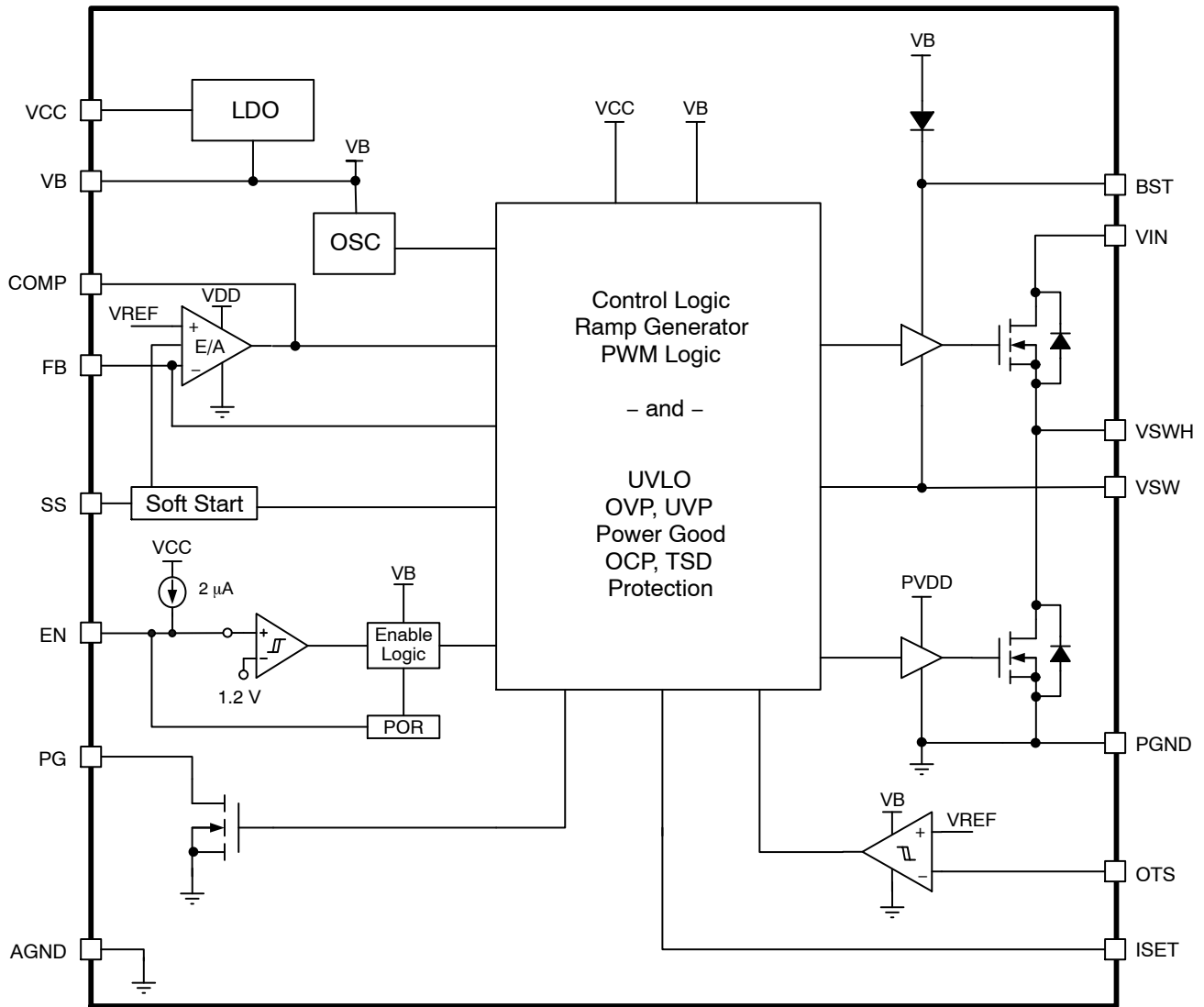


Figure 1. NCP3231B Block Diagram

NCP3231B

PIN DESCRIPTION

Pin No.	Symbol	Description
1	SS	A capacitor from this pin to GND allows the user to adjust the soft-start ramp time.
2	FB	Output voltage feedback.
3	COMP	Output of the error amplifier.
4	ISET	A resistor from this pin to ground sets the over-current protection (OCP) threshold.
5	AGND	Analog ground.
6	OTS	Negative input of internal thermal comparator. Tie this pin to ground if not in use.
7	PG	Power good indicator of the output voltage. Open-drain output. Connect PG to VDD with an external resistor.
8-14, EP42	VIN	The VIN pin is connected to the internal power NMOS switch. The VIN pin has high di/dt edges and must be decoupled to ground close to the pin of the device.
15, 29-34, EP43	VSWH	The VSWH pin is the connection of the drain and source of the internal NMOS switches. At switch off, the inductor will drive this pin below ground as the body diode and the NMOS conducts with a high dv/dt.
16-28, 37	PGND	Ground reference and high-current return path for the bottom gate driver and low-side NMOS.
35	VSW	IC connection to the switch node between the top MOSFET and bottom MOSFET. Return path of the high-side gate driver.
36	BST	Top gate driver input supply, a bootstrap capacitor connection between the switch node and this pin.
38	VB	The internal LDO output and input supply for the NCP3231B. Connect a minimum of 4.7 μ F ceramic capacitor from this pin to ground.
39	VCC	Input Supply for IC. This pin must be connected to VIN.
40	EN	Logic control for enabling the switcher. An internal pull-up enables the device automatically. The EN pin can also be driven high to turn on the device, or low to turn off the device. A comparator and precision reference allow the user to implement this pin as an adjustable UVLO circuit.
EP41	GND	Exposed Pad. Connect GND to a large copper plane at ground potential to improve thermal dissipation.

NCP3231B

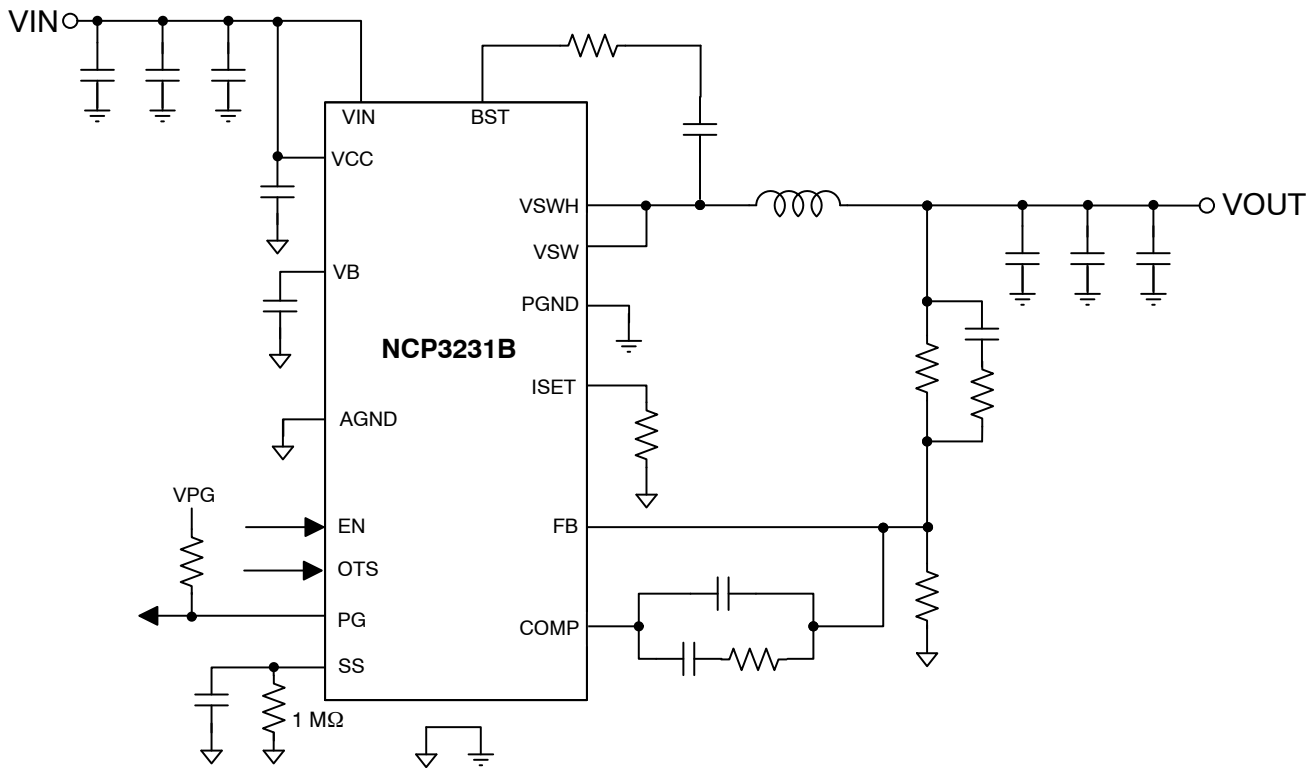


Figure 2. Typical Application Circuit

ABSOLUTE MAXIMUM RATINGS (measured vs. GND pad, unless otherwise noted)

Rating	Symbol	Value	Unit
Power Supply to GND	VIN, VCC	20.5 -0.3	V
VSW to GND	VSWH, VSW	26 -0.6 (DC) +30 (t < 50 ns) -4 (t < 100 ns)	V
BST to GND	BST	30 (DC) -0.6 (DC) +32 (t < 50 ns)	V
BST to VSW	VBST_VSW	6.5 (DC) -0.3 (DC)	V
All other pins		6.0 -0.3	V
Operating Ambient Temperature Range (Note 1)	T _A	-40 to +90	°C
Operating Junction Temperature Range (Note 1)	T _J	-40 to +150	°C
Maximum Junction Temperature	T _{J(MAX)}	+150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

THERMAL INFORMATION

HS FET Junction-to-Case Thermal Resistance (Note 2)	R _{θJC-HS}	1.3	°C/W
LS FET Junction-to-Case Thermal Resistance (Note 2)	R _{θJC-LS}	0.6	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The maximum package power dissipation limit must not be exceeded.

$$P_D = \frac{T_{J(MAX)} - T_A}{R_{\theta JA}}$$

- R_{θJC} thermal resistance is obtained by simulating a cold plate test on the exposed power pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

NCP3231B

ELECTRICAL CHARACTERISTICS

($-40^{\circ}\text{C} < T_J < +125^{\circ}\text{C}$, $V_{CC} = 12\text{ V}$, for min/max values unless otherwise noted, $T_J = +25^{\circ}\text{C}$ for typical values)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
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POWER SUPPLY

VIN/VCC Operation Voltage	VIN/VCC		4.5		18	V
VB UVLO Threshold (Rising)			4.1	4.2	4.3	V
VB UVLO Threshold (Falling)			3.4	3.66	3.8	V
VB Output Voltage	VB	$V_{CC} = 6\text{ V}, 0 \leq I_B \leq 40\text{ mA}$	4.9	5.15	5.45	V
VB Dropout Voltage		$I_B = 25\text{ mA}, V_{CC} = 4.5\text{ V}$		36	110	mV
VCC Quiescent Current		EN = H, COMP = H, no switching; PG open; no switching		4.7	6.4	mA
Shutdown Supply Current		NCP3231B; EN = 0; $V_{CC} = 18\text{ V}$; PG open		100	140	μA
		NCP3231B; EN = 0; $V_{CC} = 4.5\text{ V}$; PG open		53	75	μA

FEEDBACK VOLTAGE

FB Input Voltage	VFB	$-0^{\circ}\text{C} \leq T_J \leq 105^{\circ}\text{C}, 4.5\text{ V} \leq V_{CC} \leq 18\text{ V}$	597	600	603	mV
		$-40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C}, 4.5\text{ V} \leq V_{CC} \leq 18\text{ V}$	594	600	606	
Feedback Input Bias Current	IFB	VFB = 0.6 V			75	nA

ERROR AMPLIFIER

Open Loop DC Gain		Guaranteed by Design	60	85		dB
Open Loop Unity Gain Bandwidth	F0dB,EA			24		MHz
Open Loop Phase Margin				60		$^{\circ}$
Slew Rate		COMP pin to GND = 10 pF		2.5		V/ μ
COMP Clamp Voltage, High				3.46		V
COMP Clamp Voltage, Low				465		mV
Output Source Current		VFB = 0 V	15			mA
Output Sink Current		VFB = 1 V	20			mA

CURRENT LIMIT

Low-side $R_{DS(on)}/ISET$	$R_{DS(on)}/ISET$	Guaranteed by Characterization, $T_J = 25^{\circ}\text{C}$		44		Ω/A
Low-side ISET Current Source Temperature Coefficient	TC_LS_ISET			+0.31		%/ $^{\circ}\text{C}$
Low-side OCP Switch-over Threshold		Guaranteed by Design		600		mV
Low-side Fixed OCP Threshold	LS_OCPth	Guaranteed by Design		300		mV
Low-side Programmable OCP Range	LS_OCPth				< 600	mV
LS OCP Blanking time	LS_Tblnk	Guaranteed by Design		150		ns

PWM

Maximum duty cycle		fsw = 1 MHz, VFB = 0 V $4.5\text{ V} < V_{CC} < 18\text{ V}$		88		%
Minimum duty cycle		VCOMP < PWM Ramp Offset Voltage		0		%
Minimum GH on-time		Guaranteed by Design		40	55	ns
PWM Ramp Amplitude		Guaranteed by Characterization	VCC/8.6	VCC/6.6	VCC/5.6	V
PWM Ramp Offset		Guaranteed by Characterization		0.64		V

OSCILLATOR

Oscillator Frequency Range	fsw	fsw = 1 MHz $4.5\text{ V} < V_{CC} < 18\text{ V}$	950	1000	1050	kHz
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NCP3231B

ELECTRICAL CHARACTERISTICS

($-40^{\circ}\text{C} < T_J < +125^{\circ}\text{C}$, $V_{CC} = 12\text{ V}$, for min/max values unless otherwise noted, $T_J = +25^{\circ}\text{C}$ for typical values)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
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OSCILLATOR

Hiccup Timer	t_{hiccup}	$t_{\text{ss}} < 1\text{ ms}$, $f_{\text{sw}} = 1\text{ MHz}$		4		ms
		$t_{\text{ss}} > 1\text{ ms}$, $f_{\text{sw}} = 1\text{ MHz}$		4 x t_{ss}		ms

ENABLE INPUT (EN)

EN Input Operating Range					5.5	V
Enable Threshold Voltage	V_{EN}	VEN rising	1.11	1.2	1.29	V
Enable Hysteresis		VEN falling		144		mV
Deep Disable Threshold			0.7	0.78	0.9	V
Enable Pull-up Current				2		μA

SOFTSTART INPUT (SS)

SS Startup Delay	t_{SSD}			0.75		ms
SS End Threshold	SSEND			0.6		V
SS Source Current	ISS		2.15	2.5	2.8	μA

VOLTAGE MONITOR

Power Good Sink Current		PG = 0.15 V	10	20	30	mA
Output Overvoltage Rising Threshold			665	675	685	mV
Overvoltage Fault Blanking Time				20		μs
Output Under-Voltage Trip Threshold			500	525	550	mV
Under-voltage Protection Blanking Time				20		μs
OVP and UVP Enable Delay				t_{SS}		s

POWER STAGE

High-side On Resistance	RDSONH	$V_{\text{IN}}/V_{\text{CC}} = 5\text{ V}$, $I_{\text{D}} = 2\text{ A}$		7	9.9	$\text{m}\Omega$
Low-side On Resistance	RDSONL	$V_{\text{IN}}/V_{\text{CC}} = V_{\text{B}}$, $I_{\text{D}} = 2\text{ A}$		1.5	2.9	$\text{m}\Omega$
VFBOOT		I _{BOOT} = 2 mA		28		mV

THERMAL MONITOR (OTS)

OTS comparator reference voltage (Rising Threshold)			0.58	0.62	0.65	V
OTS comparator reference voltage (Falling Hysteresis)				50		mV

THERMAL SHUTDOWN

Thermal Shutdown Threshold		Guaranteed by design	135	150	165	$^{\circ}\text{C}$
Thermal Shutdown Hysteresis		Guaranteed by design		25		$^{\circ}\text{C}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

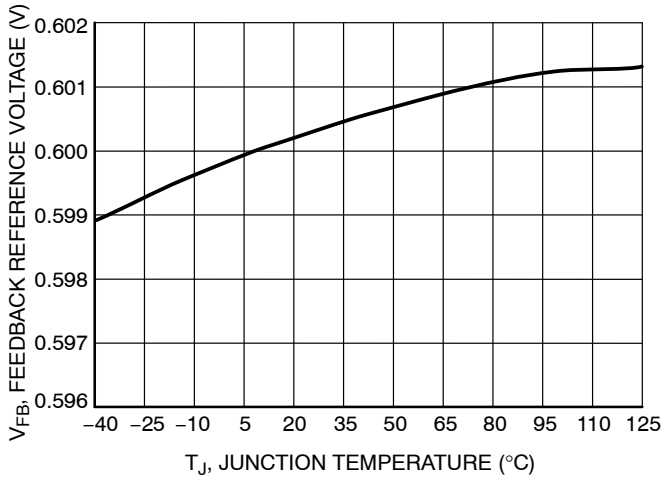


Figure 3. Reference Voltage vs. Temperature

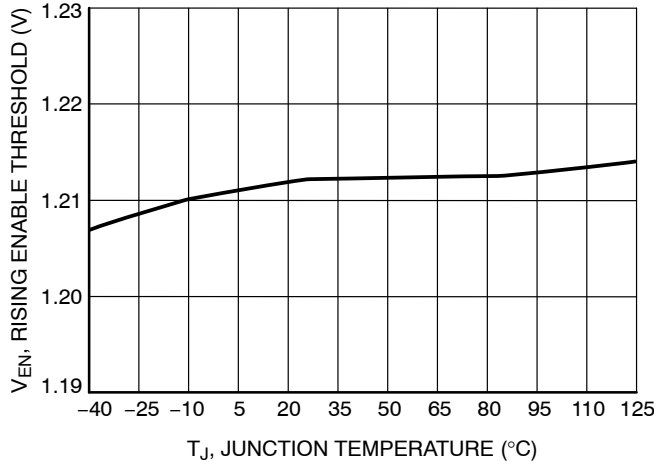


Figure 4. Rising Enable Threshold vs. Temperature

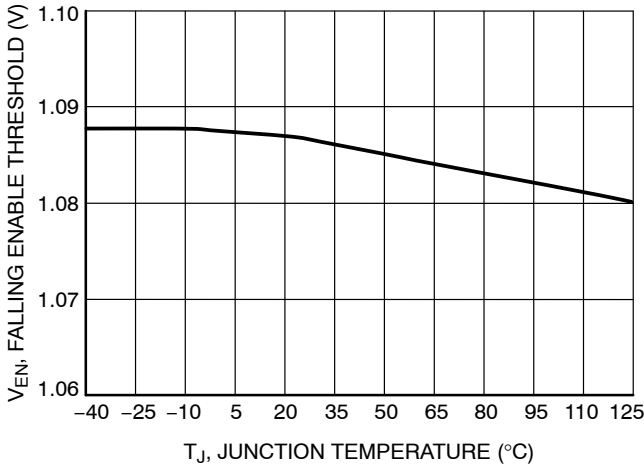


Figure 5. Falling Enable Threshold vs. Temperature

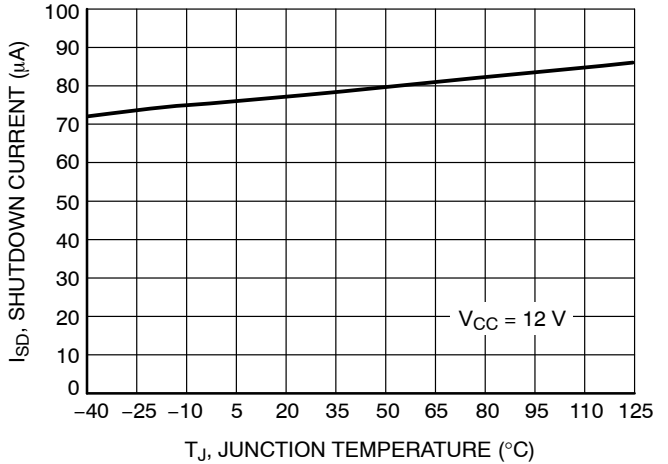


Figure 6. Shutdown Current vs. Temperature

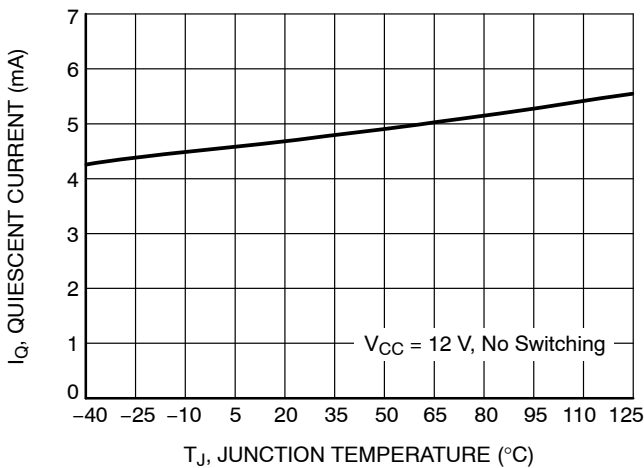


Figure 7. Quiescent Current vs. Temperature

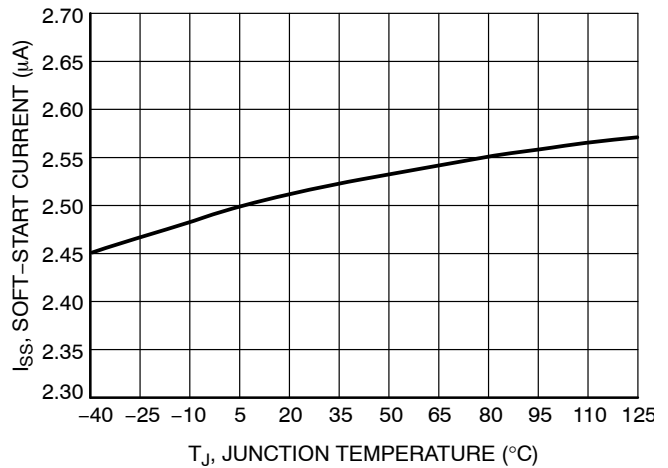


Figure 8. Soft-start Current vs. Temperature

TYPICAL CHARACTERISTICS

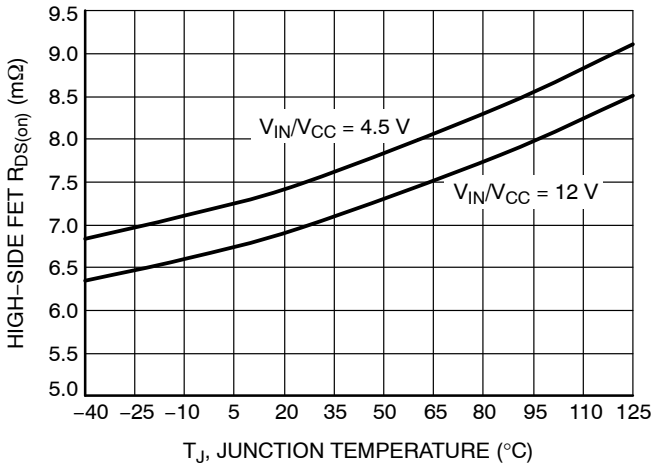


Figure 9. High-side R_{DS(on)} vs. Temperature

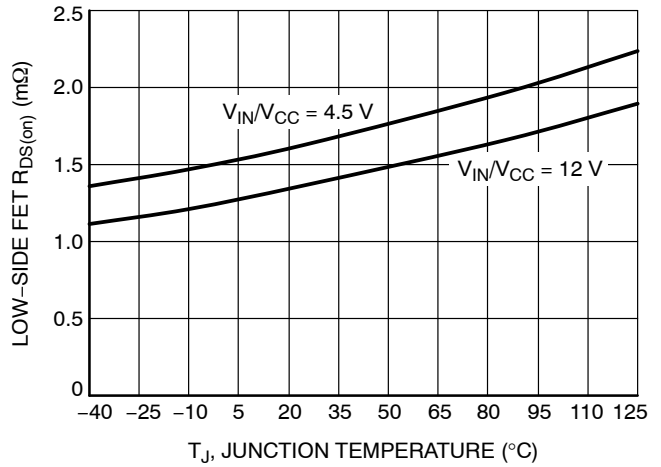


Figure 10. Low-side R_{DS(on)} vs. Temperature

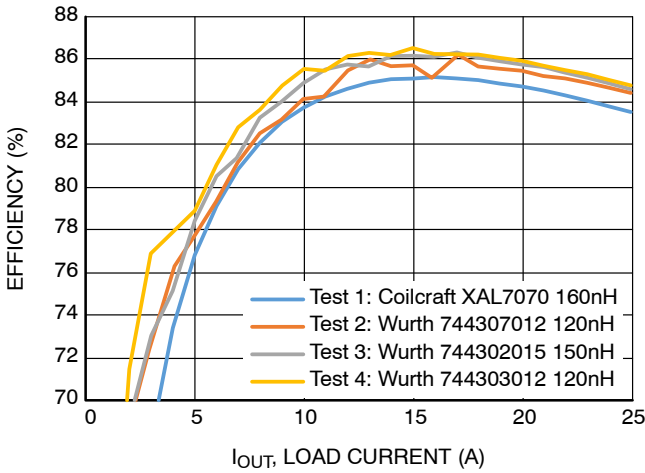


Figure 11. Efficiency vs. I_{out}
(V_{in} = 12 V to 1.0 V)

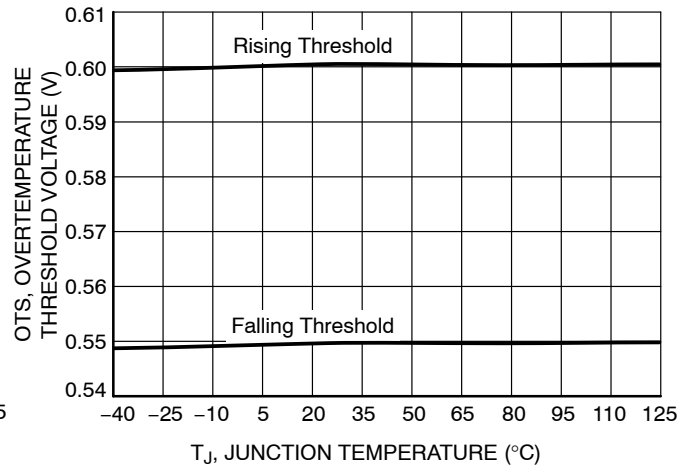


Figure 12. OTS Threshold vs. Temperature

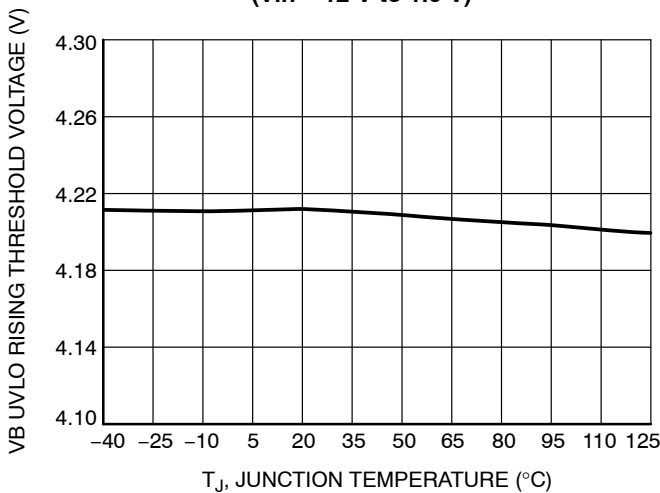


Figure 13. VB UVLO Rising Threshold vs. Junction Temperature

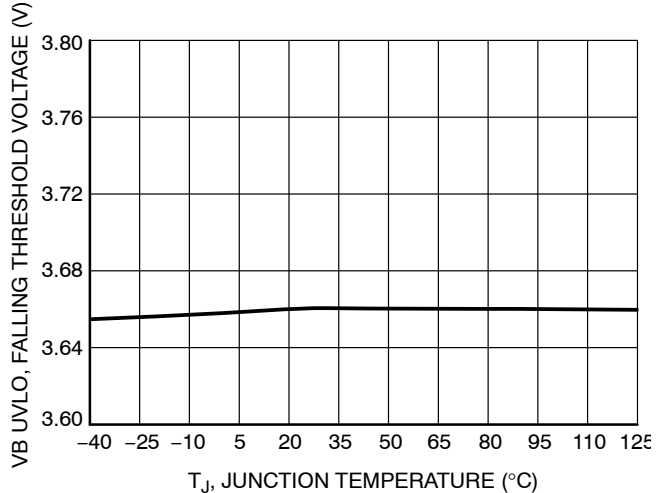


Figure 14. VB UVLO Falling Threshold vs. Junction Temperature

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TYPICAL CHARACTERISTICS

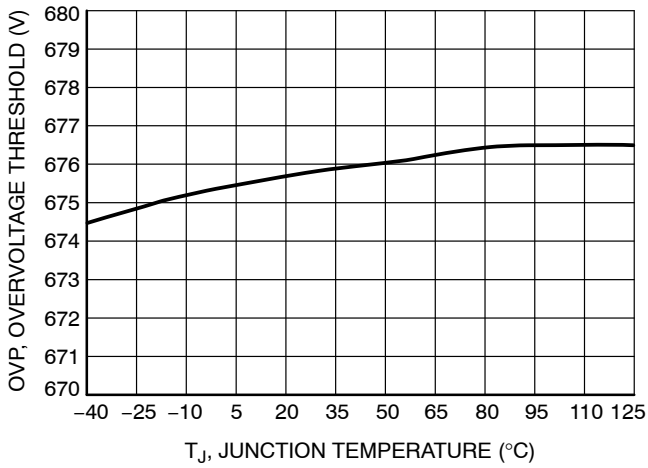


Figure 15. Output OVP vs. Junction Temperature

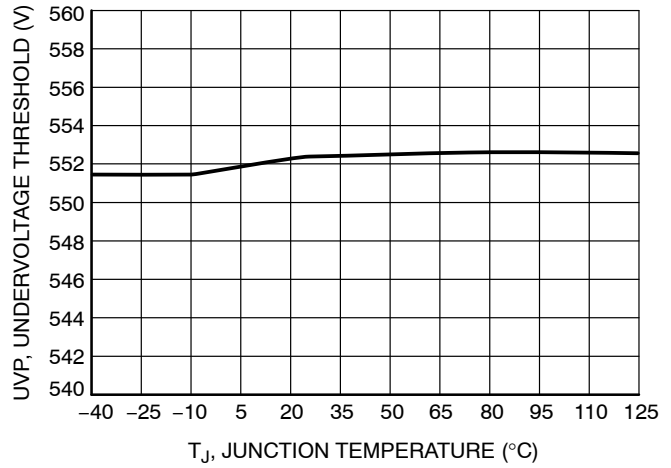
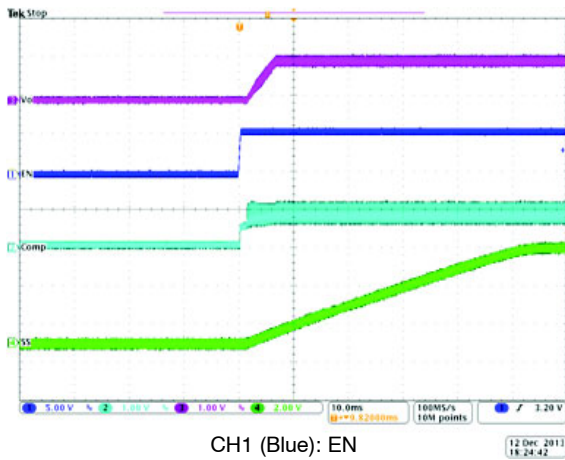
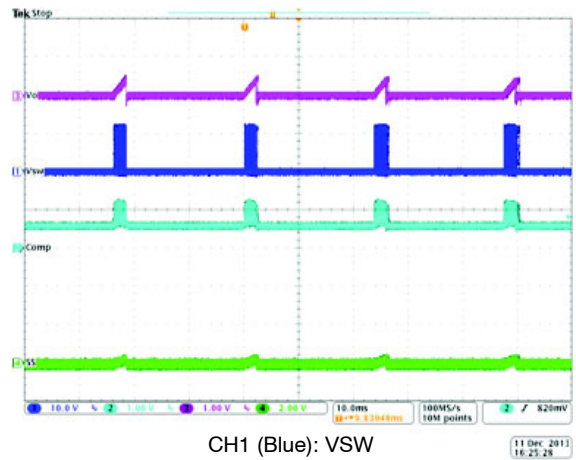


Figure 16. Output UVP vs. Junction Temperature



CH1 (Blue): EN
 CH2 (Aqua): COMP
 CH3 (Purple): Vout
 CH4 (Green): SS

Figure 17. Typical Startup Waveforms
 (V_{in} = 12 V, I_{out} = 25 A, V_{out} = 1 V)



CH1 (Blue): VSW
 CH2 (Aqua): COMP
 CH3 (Purple): Vout
 CH4 (Green): SS

Figure 18. Typical Short Circuit Waveforms
 (V_{in} = 12 V)

OPERATION DESCRIPTION

Overview

The NCP3231B is a 1 MHz, high efficiency, high current PWM synchronous buck converter. It operates with a single supply voltage from 4.5 to 18 V and can provide output current as high as 25 A. NCP3231B utilizes voltage mode with voltage feed-forward control to respond instantly to Vin changes and provide for easier compensation over the supply range of the converter. The device also includes pre-bias startup capability to allow monotonic startup in the event of a pre-biased output condition.

Protection features include overcurrent protection (OCP), output over and under voltage protection (OVP, UVP), and power good. The enable function is highly programmable to allow for adjustable startup voltages at higher input voltages. There is also an adjustable soft-start, an over-temperature/over-voltage comparator, and internal thermal shutdown.

Reference Voltage

The NCP3231B incorporates an internal reference that allows output voltages as low as 0.6 V. The tolerance of the internal reference is guaranteed over the entire operating temperature range of the controller. The reference voltage is trimmed using a test configuration that accounts for error amplifier offset and bias currents.

Oscillator Ramp

The ramp waveform is a saw tooth formed at the PWM frequency with a peak-to-peak amplitude of VCC/6.6, offset from GND by typically 0.64 V. The PWM duty cycle is limited to a maximum of 92%, allowing the bootstrap capacitor to charge during each cycle.

Error Amplifier

The error amplifier’s primary function is to regulate the converter’s output voltage using a resistor divider connected from the converter’s output to the FB pin of the controller, as shown in the Applications Schematic. A type III compensation network must be connected around the error amplifier to stabilize the converter. It has a bandwidth of greater than 24 MHz, with open loop gain of at least 60 dB.

Programmable Soft-Start

An external capacitor connected from the SS pin to ground sets up the soft start period, which can limit the start-up inrush current. The soft start period can be programmed based on the Equation 1.

$$t_{SS} = \frac{C_{SS} \times V_{ref}}{I_{SS}} \quad (\text{eq. 1})$$

OCP is the only fault that is active during a soft-start.

Adaptive Non-Overlap Gate Driver

In a synchronous buck converter, a certain dead time is required between the low side drive signal and high side

drive signal to avoid shoot through. During the dead time, the body diode of the low side FET freewheels the current. The body diode has much higher voltage drop than that of the MOSFET, which reduces the efficiency significantly. The longer the body diode conducts, the lower the efficiency. NCP3231B implements adaptive dead time control to minimize the dead time, as well as preventing shoot through.

Precision Enable (EN)

The ENABLE block allows the output to be toggled on and off and is a precision analog input.

When the EN voltage exceeds V_EN, the controller will initiate the soft-start sequence as long as the input voltage and sub-regulated voltage have exceeded their UVLO thresholds. V_EN_hyst helps to reject noise and allow the pin to be resistively coupled to the input voltage or sequenced with other rails.

If the EN voltage is held below typically 0.8 V, the NCP3231B enters a deep disable state where the internal bias circuitry is off. As the voltage at EN continues to rise, the Enable comparator and reference are active and provide a more accurate EN threshold. The drivers are held off until the rising voltage at EN crosses V_EN.

An internal 2 μA pullup automatically enables the device when the EN pin is left floating.

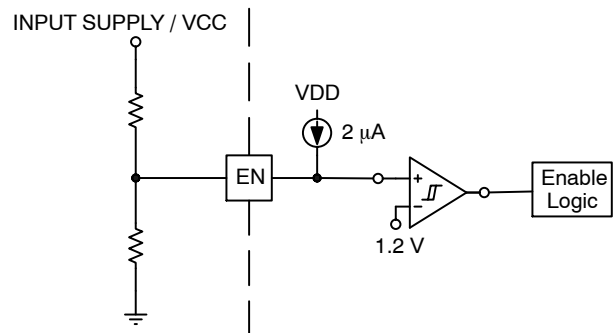


Figure 19. Enable Functional Block Diagram

Pre-bias Startup

In some applications the controller will be required to start switching when its output capacitors are charged anywhere from slightly above 0 V to just below the regulation voltage. This situation occurs for a number of reasons: the converter’s output capacitors may have residual charge on them or the converter’s output may be held up by a low current standby power supply. NCP3231B supports pre-bias start up by holding off switching until the feedback voltage and thus the output voltage rises above the set regulated voltage. If the pre-bias voltage is higher than the set regulated voltage, switching does not occur until the output voltage drops back to the regulation point.

NCP3231B

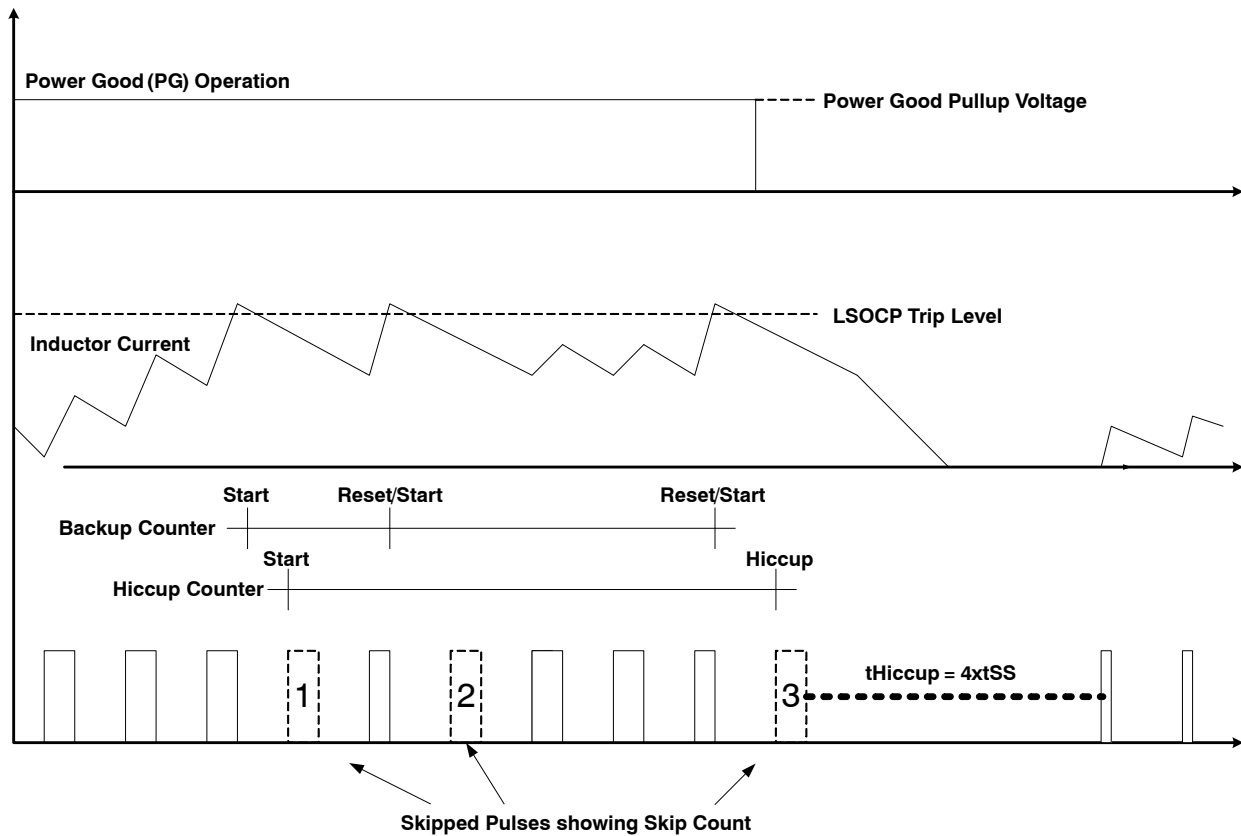


Figure 20. LSOCP Function with Counters and Power Good Shown (exaggerated for informational purposes)

PROTECTION FEATURES

Hiccup Mode

The NCP3231B utilizes hiccup mode for all of its fault conditions. Upon entering hiccup mode after a fault detection, the NCP3231B turns off the high side and low side FET's and PG goes low. It waits for t_{HICCUP} ms before reinitiating a soft-start. t_{HICCUP} is defined as four soft start timeouts (tss). And if the soft-start time tss is set to be less than 1 ms, the hiccup time will be 4 ms. The equation for tss is shown in Equation 1. OCP is the only active fault detection during the hiccup mode soft start.

Over Temperature Comparator (OTS)

The NCP3231B provides an over-temperature shutdown (OTS) comparator with 50 mV hysteresis and a 0.6 V reference in order to remotely sense an external temperature detector or thermistor. When the voltage at the OTS pin rises above 0.6 V, the drivers stop switching and both FET's remain off. When this voltage drops below typically 0.55 V, a new soft-start cycle is generated automatically. Tie the OTS pin to ground if this function is not required.

Over Voltage Protection (OVP)

When the voltage at the FB pin (VFB) is above the OVP threshold for greater than 20 μ s (typical), an OVP fault is set. The high side FET (HSFET) will turn off and the low side FET (LSFET) will turn on. The open-drain PG pull down

will turn on at that point as well, thus pulling PG low. Once VFB has fallen below the Undervoltage Protection Threshold (UVP), the device will enter hiccup mode.

Under Voltage Protection (UVP)

A UVP circuit monitors the VFB voltage to detect an under voltage event. If the VFB voltage is below this threshold for more than 20 μ s, a UVP fault is set and the device will enter hiccup mode.

Over Current Protection (OCP)

The NCP3231B over current protection scheme senses the peak freewheeling current in the low-side FET (LSOCP) after a blanking time of 150 ns as shown in Figure 20. The low-side FET drain-to-source voltage, V_{DS} , is compared against the voltage of a fixed, internal current source, ISET and a user-selected resistor, RSET. Voltage across the low-side FET is sensed from the VSW pin to GND.

After an OCP detection, the NCP3231B keeps the high-side FET off until the Low-side FET current falls below the trip point again and the next clock cycle occurs. An internal OCP counter will count up to 3 consecutive LSOCP events. After the third consecutive count, the device enters hiccup mode.

To prevent nuisance trips, there is a backup counter that will reset the OCP counter after 7 consecutive cycles without an LSOCP trigger. The backup counter is reset and then started again after each OCP trip until the third OCP count as stated above occurs.

Over Current Protection Threshold

The NCP3231B allows the user to adjust the LSOCP threshold with an external resistor, RSET. This resistor, along with an internal temperature compensated current source, ISET, sets the current limit reference voltage for the LSOCP comparator.

Internally, a current sense circuit samples the voltage from VSW to GND. This voltage is then multiplied by a factor of 2 and compared against the ISET*RSET voltage threshold.

The basic design equation for LSOCP trip point selection is:

$$\begin{aligned} RSET &= \frac{3 \times (i_{Load} + 0.5i_{Lpk-pk}) \times R_{dson}}{ISET} \quad (\text{eq. 2}) \\ &= 3 \times 44 \times (i_{Load} + 0.5i_{Lpk-pk}) \end{aligned}$$

In this equation, i_{Load} is the over current protection point of the load current, i_{Lpk-pk} is the peak to peak value of inductor current, and for example, when input voltage is 12 V, output voltage is 3.3 V, switching frequency is 1 MHz and inductor value is 330 nH, the peak to peak value of inductor current is 14.5 A. ISET is temperature compensated current source proportional to the on-resistance of LS MOSFET, R_{dson} , the ratio of R_{dson} to ISET is about 44.

In case RSET is not connected, the device switches the OCP threshold to a fixed 300 mV value: an internal safety clamp on ISET is triggered as soon as the ISET voltage reaches 600 mV, enabling the 300 mV fixed threshold.

Thermal Shutdown (TSD)

The NCP3231B protects itself from overheating with an internal thermal monitoring circuit. If the junction temperature exceeds the thermal shutdown threshold both the upper and lower MOSFETs will be shut OFF. Once the temperature drops below the falling hysteresis threshold, the voltage at the COMP pin will be pulled below the ramp valley voltage and a soft-start will be initiated.

Power Good Monitor (PG)

NCP3231B monitors the output voltage and signal when the output is out of regulation or during a non-regulated pre-bias condition, or fault condition. When the output voltage is within the OVP and UVP thresholds, the power

good pin is a high impedance output. If the NCP3231B detects an OCP, OVP, UVP, OTS, TSD or is in soft start, it pulls PG pin low. The PG pin is an open drain 10 mA pull down output.

Layout Guidelines

When laying out a power PCB for the NCP3231B there are several general key points and special key points to consider:

General Layout Guide: these are the common techniques for high frequency high power board layout design.

Base component placement: High current path components should be placed to keep the current path as tight as possible. Placement of components on the bottom of the board such as input or output decoupling can add loop inductance.

Ground Return for Power and Signals: Solid, uninterrupted ground planes must be present and adjacent to the high current path.

Copper Shapes on Component Layers: Large copper planes on one or multiple layers with adequate vias will increase thermal transfer, reduce copper conduction losses, and minimize loop inductance. Greater than 20 A designs require 2~3 layer shapes or more, increasing the number of layers will only improvement performance.

Via Placement for Power and Ground: Place enough vias to adequately connect outer layers to inner layers for thermal transfer and to minimize added inductance in layer transition. Multiple vias should be placed near important components like input ceramics and output ceramic capacitors.

Key Signal Routes: Do not route sensitive signals, such as FB near or under noisy nets such as the switch node VSW and BST node, to reduce noise coupling effects on the sensitive lines.

Special Layout Guide: please pay attention to the special requirement of layout guide.

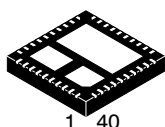
To improve the High-side OCP accuracy, users should connect VCC and VIN directly and do not place any type of filter or resistor between these two pins.

To improve the Low-side OCP accuracy, users should use single ground connection instead of separate analog ground and power ground. Make sure that the inner layers (at least 2nd layer, 3rd layer and 4th layer) are dedicated for ground plane. Do not use other copper planes to cut or interrupt the shape of ground plane, which may add more parasitic components to affect the sensing accuracy.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

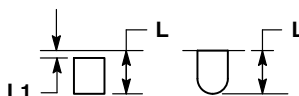
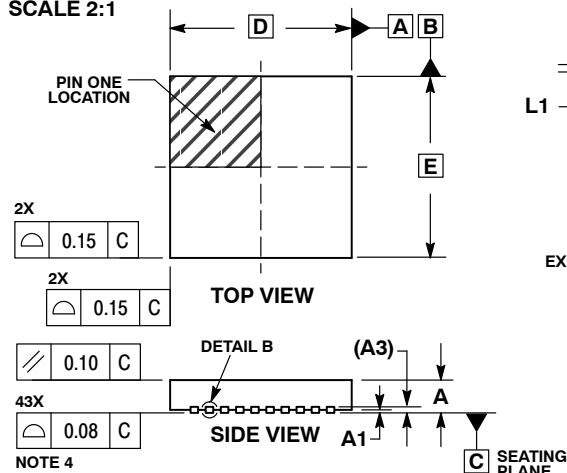
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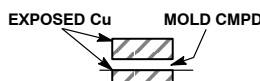
1 40
SCALE 2:1

QFN40 6x6, 0.5P
CASE 485CM
ISSUE O

DATE 05 JUN 2012



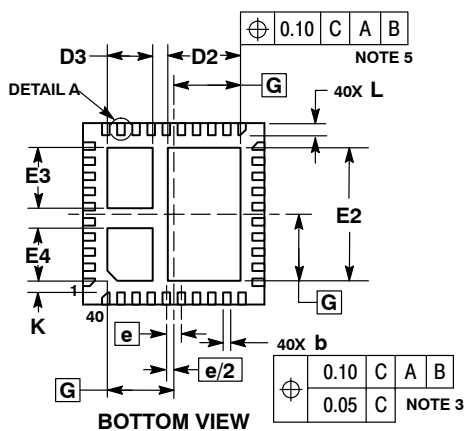
DETAIL A
ALTERNATE
CONSTRUCTIONS



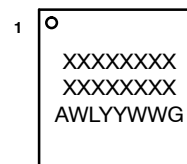
DETAIL B
ALTERNATE
CONSTRUCTION

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSIONS: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL
 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
 5. POSITIONAL TOLERANCE APPLIES TO ALL THREE EXPOSED PADS.

MILLIMETERS		
DIM	MIN	MAX
A	0.80	1.00
A1	---	0.05
A3	0.20	REF
b	0.18	0.30
D	6.00	BSC
D2	2.30	2.50
D3	1.40	1.60
E	6.00	BSC
E2	4.30	4.50
E3	1.90	2.10
E4	1.64	1.84
e	0.50	BSC
G	2.20	BSC
K	0.20	---
L	0.30	0.50
L1	---	0.15

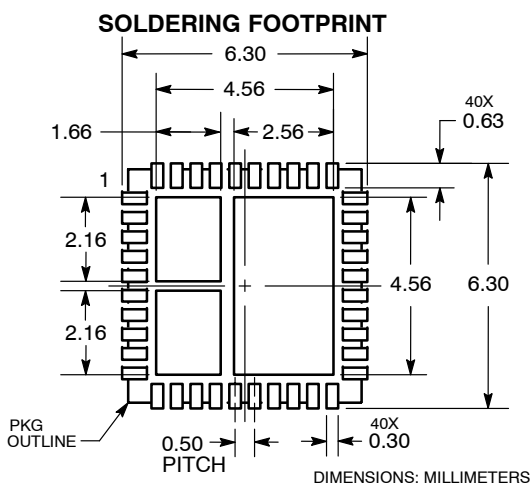


GENERIC MARKING DIAGRAM*



- XXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.



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DESCRIPTION:	QFN40 6x6, 0.5P	PAGE 1 OF 1

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